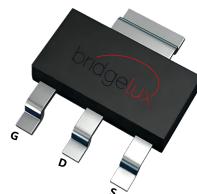
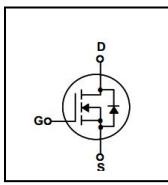


100V 3.9A N-Channel Enhancement Mode Power MOSFET**FEATURES**

- $R_{DS(on)} \leq 115\text{m}\Omega$ @ $V_{GS} = 10\text{V}$, $I_D = 3\text{A}$
- Advanced SGT process
- Excellent $R_{DS(on)}$ and Low Gate Charge
- Lead free product is acquired

APPLICATION

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

SYMBOL**SOT-223-3L****ASSEMBLY MESSAGE**

Product Name	Package	Packaging
BXS1150N10N	SOT-223-3L	Reel

ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Rating		Unit
		SOT-223-3L		
Drain-Source Voltage	V_{DSS}	100		V
Drain Current	I_D	3.9		A
		2.6		A
Drain Current	I_{DM}	15.6		A
Gate-Source Voltage	V_{GSS}	± 20		V
Power Dissipation	P_D	2.7		W
Maximum Junction Temperature	T_J	150		$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 to 150		$^\circ\text{C}$

Note: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

THERMAL CHARACTERISTICS

Parameter	Symbol	Max.		Unit
		SOT-223-3L		
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	46.3		$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_J=25^\circ\text{C}$, unless otherwise Noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$\text{VGS}=0\text{V}, \text{ID}=250\mu\text{A}$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$\text{VDS}=100\text{V}, \text{VGS}=0\text{V}$			1	μA
Gate-Body Leakage Current, Forward	I_{GSS}	$\text{VGS}=20\text{V}$			100	nA
Gate-Body Leakage Current, Reverse		$\text{VGS}=-20\text{V}$			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$\text{V}_{\text{GS(TH)}}$	$\text{VDS}=\text{VGS}, \text{ID}=250\mu\text{A}$	1.2	1.6	2.5	V
Drain-Source On-State Resistance	$\text{R}_{\text{DS(ON)}}$	$\text{VGS}=10\text{V}, \text{ID}=3\text{A}$		100	115	$\text{m}\Omega$
		$\text{VGS}=4.5\text{V}, \text{ID}=2\text{A}$		140	190	$\text{m}\Omega$
DYNAMIC PARAMETERS						
Input Capacitance	C_{iss}	$\text{VDS}=50\text{V}, \text{VGS}=0\text{V}, \text{f}=1.0\text{MHz}$		790		pF
Output Capacitance	C_{oss}			42		pF
Reverse Transfer Capacitance	C_{rss}			30		pF
SWITCHING PARAMETERS						
Turn-ON Delay Time	$t_{\text{D(ON)}}$	$\text{VDD}=50\text{V}, \text{ID}=3.9\text{A}, \text{VGS} = 10\text{V}, \text{RG}=3\Omega$		6.1		ns
Turn-ON Rise Time	t_{R}			41.2		ns
Turn-OFF Delay Time	$t_{\text{D(OFF)}}$			24.5		ns
Turn-OFF Fall-Time	t_{F}			8.2		ns
Total Gate Charge(Note3)	Q_{G}	$\text{VDS} = 50\text{V}, \text{VGS} = 10\text{V}, \text{ID} = 2\text{A}$		16.3		nC
Gate Source Charge	Q_{GS}			2.6		nC
Gate Drain Charge	Q_{GD}			2.8		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Drain-Source Diode Forward Voltage	V_{SD}	$\text{IS}=1\text{A}, \text{VGS}=0\text{V}$		0.8	1.2	V
Diode Continuous Forward Current	I_{s}				3.9	A

Note: 2. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

3. Essentially independent of operating temperature

TYPICAL CHARACTERISTICS

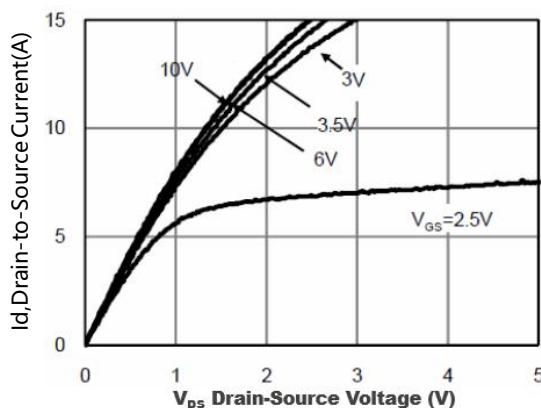


Figure1. Typical Output Characteristics

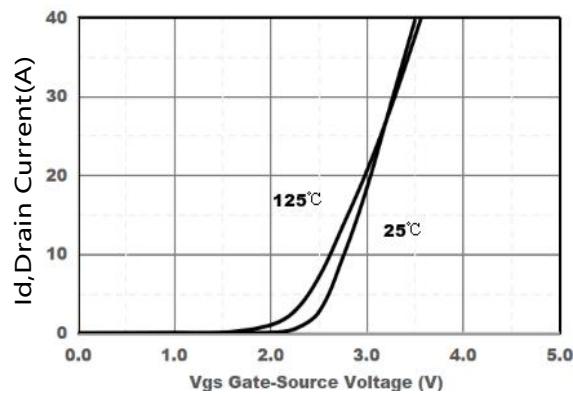


Figure2. Typical Transfer Characteristics

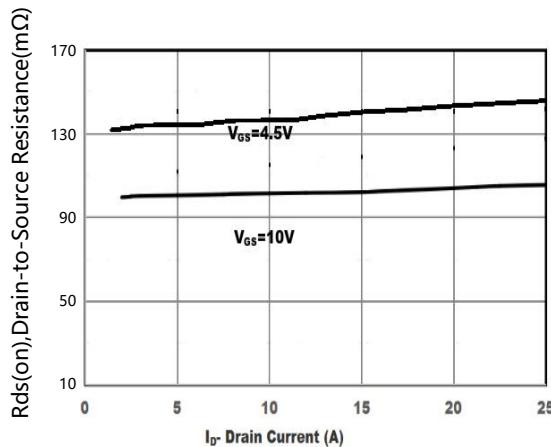


Figure3. On-Resistance versus Drain Current

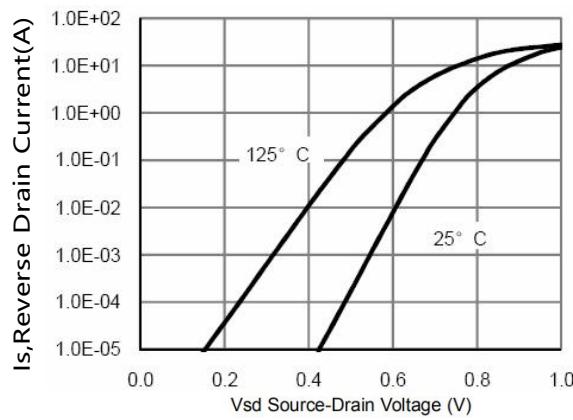
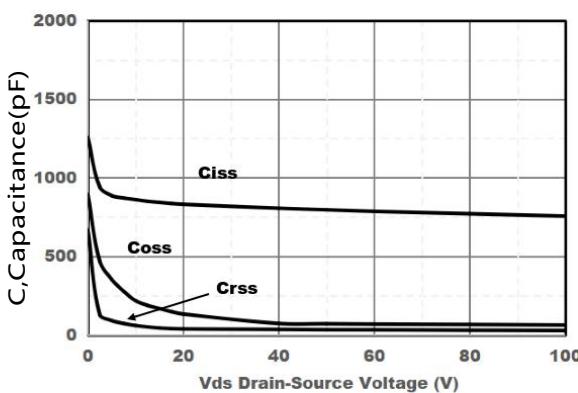
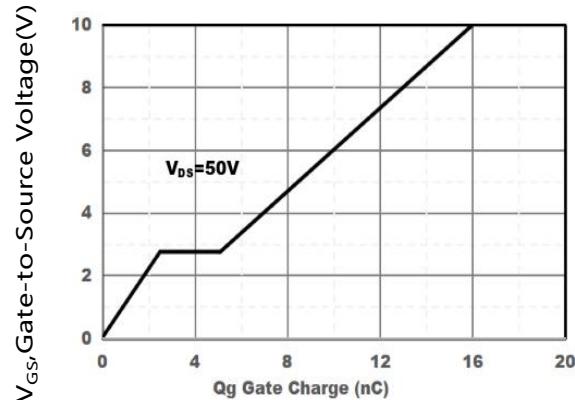
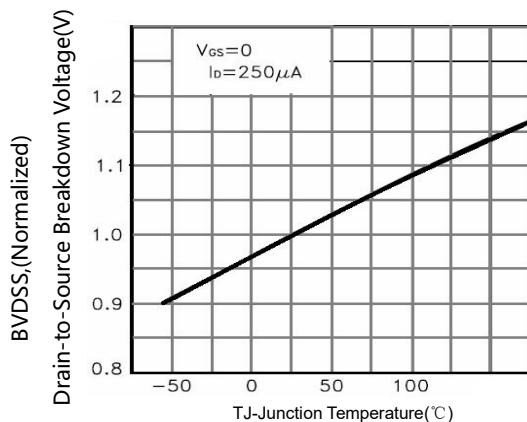
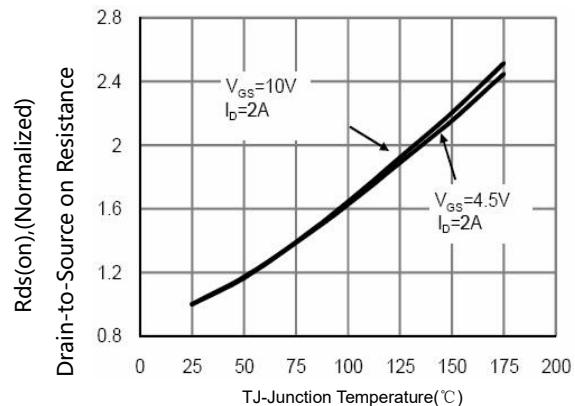
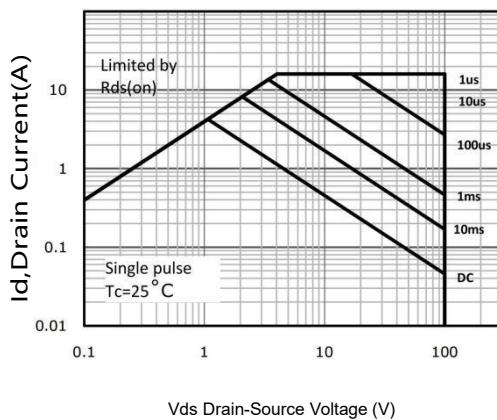
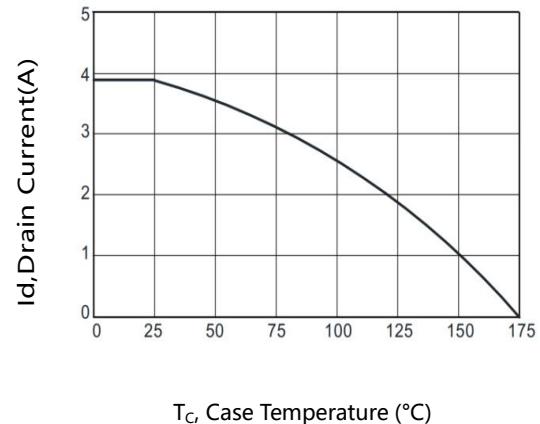
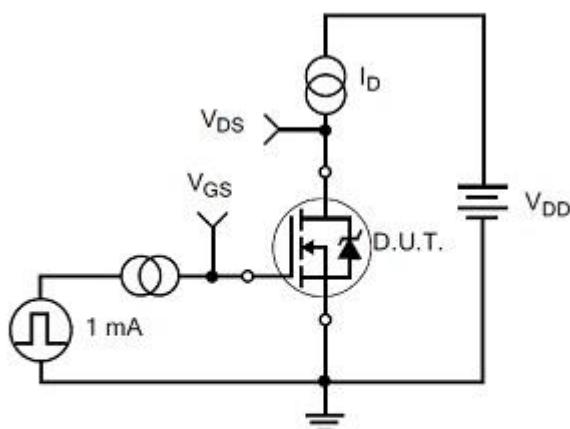


Figure4. Diode forward voltage versus Current

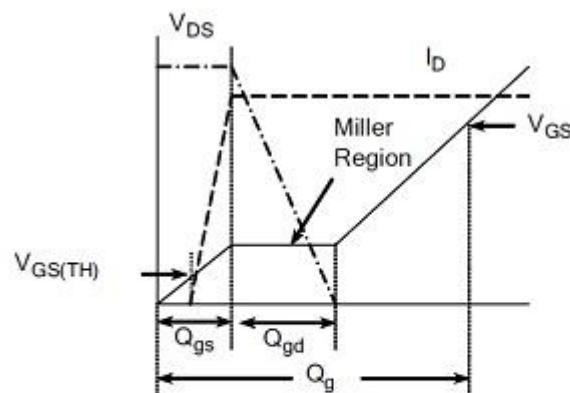
Figure5. Typical Capacitance versus V_{ds} Figure6. Typical Gate Charge versus V_{gs}

TYPICAL CHARACTERISTICS(Cont.)

Figure7. BV_{DSS} Variation with Temperature

Figure8. On-Resistance Variation with Temperature

Figure9. Maximum Safe Operating Area

Figure10. Maximum Continuous Drain Current versus Case Temperature

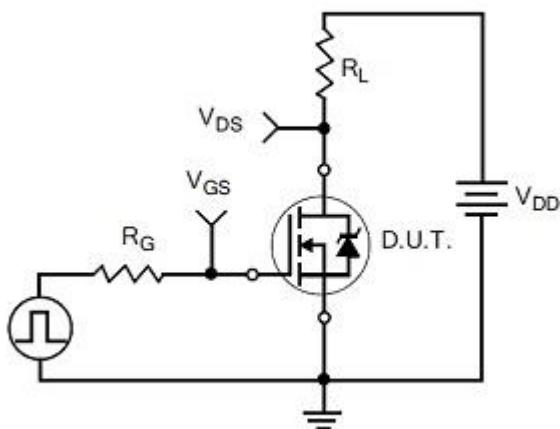
TEST CIRCUITS AND WAVEFORMS



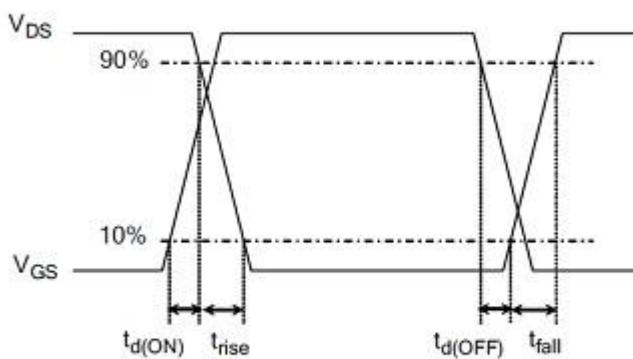
Gate Charge Test Circuit



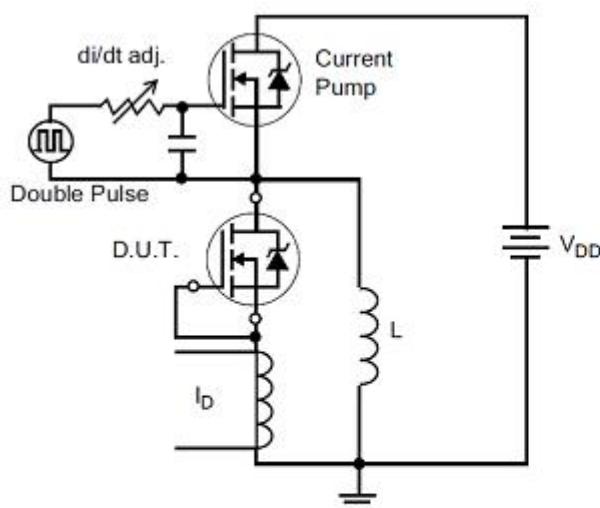
Gate Charge Waveform



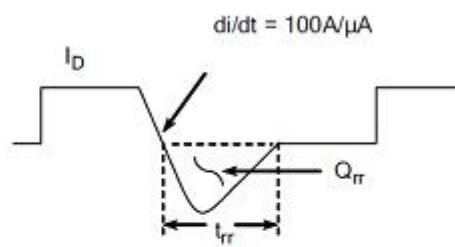
Resistive Switching Test Circuit



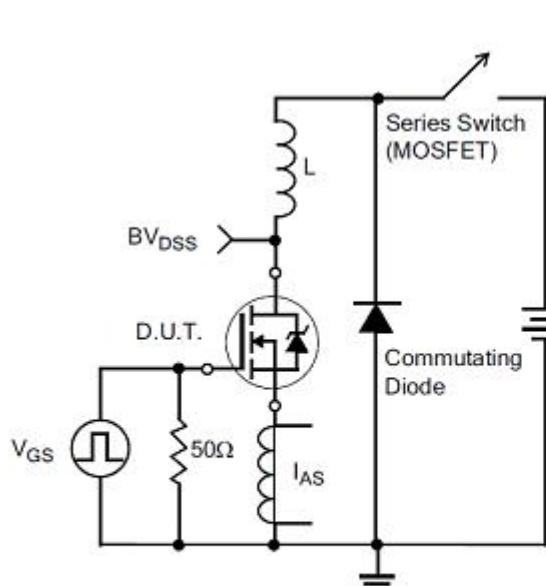
Resistive Switching Waveforms



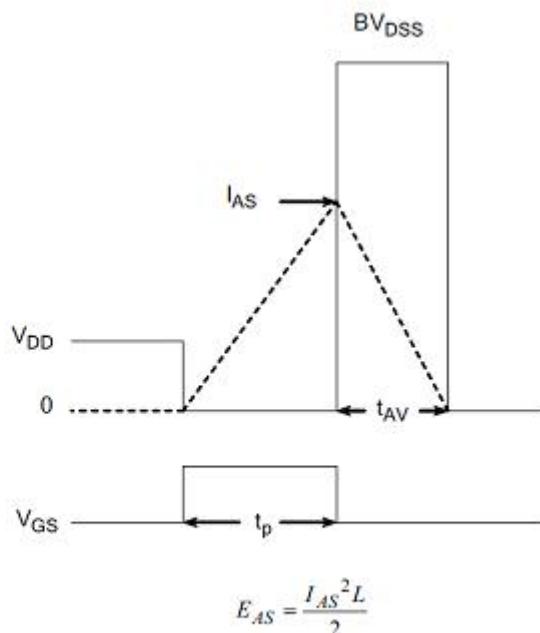
Diode Reverse Recovery Test Circuit



Diode Reverse Recovery Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



Bridgelux WuXi R&D CO., LTD

Halogen Free

BXS1150N10N

Revision history

Document revision history

Date	Revision	Changes
15-Nov-2021	1.0	First release

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